

Appl. No. 10/725,050  
Examiner: FENTY, JESSE A, Art Unit 2815  
Supplemental amendment in response to the Office Action  
dated March 22, 2005

Date: July 7, 2005  
Attorney Docket No. 10111682

#### AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 7, line 15 with the following amended paragraph:

— The multiple tip floating gate 203c of the present invention is composed of a conductive base 203d and a conductive protruding layer 203e. The conductive base 203d has a first top portion and a first bottom portion, wherein an edge of the first top portion is a tip, ~~and the first bottom portion contacts the semiconductor substrate 201.~~ A gate dielectric layer 202a is formed between the first bottom portion and the semiconductor substrate 201. The conductive protruding layer 203e protrudes from the conductive base 203d, and the conductive protruding layer 203e has a flat top. The conductive protruding layer 203e has a second top portion and a second bottom portion, wherein the second top portion is a second tip, and the second bottom contacts the first top portion. The conductive protruding layer 203e has two concave sidewalls. A multiple tip floating gate is composed of the conductive base 203d and the conductive protruding layer 203e.